

Features

- Split Gate Trench Mosfet Technology
- Excellent Package For Good Heat Dissipation
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device ^(Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-CHANNEL MOSFET

Maximum Ratings

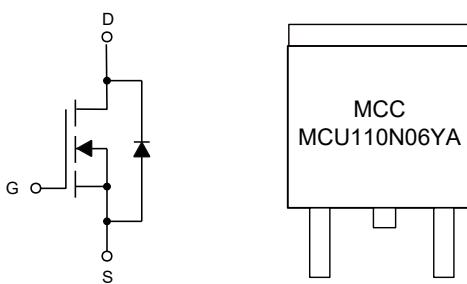
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 50°C/W Junction to Ambient ^(Note2)
- Thermal Resistance: 1.4°C/W Junction to Case

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current T _C =25°C	I _D	110	A
T _C =100°C		70	
Pulsed Drain Current ^(Note3)	I _{DM}	440	A
Total Power Dissipation ^(Note4)	P _D	89	W
Single Pulse Avalanche Energy ^(Note5)	E _{AS}	722	mJ

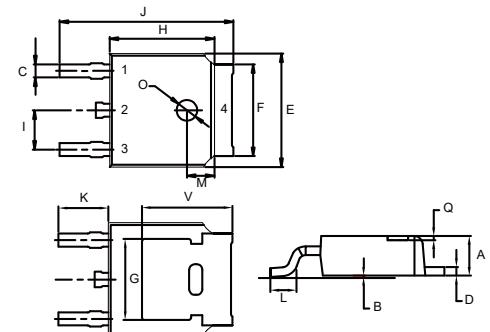
Note:

1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. T_J=25°C, V_{DD}=30V, V_{GS}=10V, R_G=25Ω, L=4mH.

Internal Structure and Marking Code



DPAK(TO-252)



1. Gate
2,4. Drain
3. Source

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.087	0.094	2.20	2.40	
B	0.000	0.005	0.00	0.13	
C	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
E	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
H	0.236	0.244	6.00	6.20	
I	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.047	0.069	1.20	1.75	
M	0.063		1.60		TYP.
O	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	60			V
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.7	2.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =55A		3.2	4.4	mΩ
		V _{GS} =4.5V, I _D =20A		3.7	5	
Gate Resistance	R _g	f=1 MHz, Open drain		2.3		Ω
Diode Characteristics						
Continuous Body Diode Current	I _S				110	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =55A			1.2	V
Reverse Recovery Time	t _{rr}	I _F =25A, dI/dt=100A/μs		51		ns
Reverse Recovery Charge	Q _{rr}			56		nC
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, f=500KHz		5233		pF
Output Capacitance	C _{oss}			1050		
Reverse Transfer Capacitance	C _{rss}			2.1		
Total Gate Charge	Q _g	V _{DS} =50V, V _{GS} =10V, I _D =50A		80		nC
Gate-Source Charge	Q _{gs}			15		
Gate-Drain Charge	Q _{gd}			12		
Turn-On Delay Time	t _{d(on)}	V _{DD} =30V, V _{GS} =10V, R _G =2Ω, I _{DS} =25A		13		ns
Turn-On Rise Time	t _r			36		
Turn-Off Delay Time	t _{d(off)}			54		
Turn-Off Fall Time	t _f			19		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

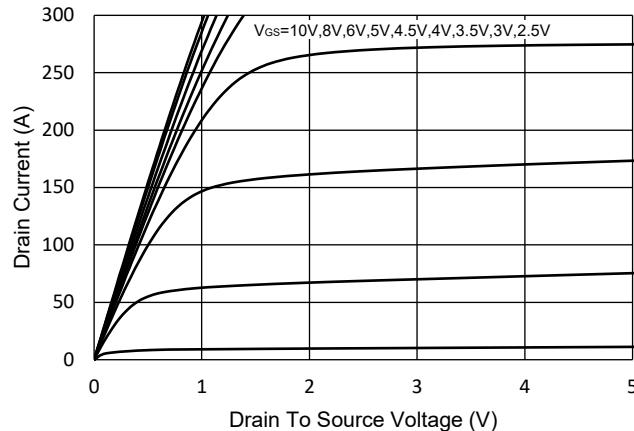


Fig. 2 - Transfer Characteristics

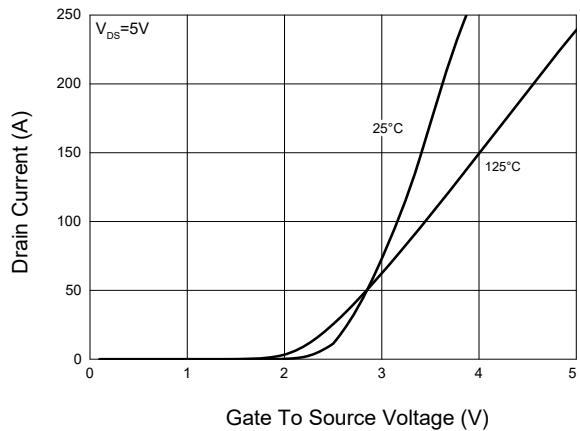


Fig.3 - $R_{DS(ON)}$ - V_{GS}

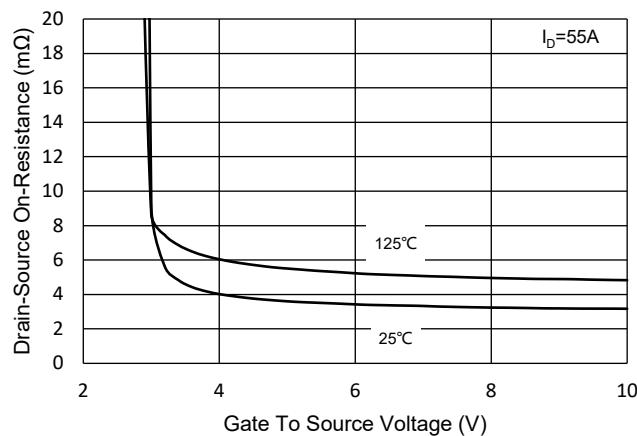


Fig. 4 - $R_{DS(ON)}$ — I_D

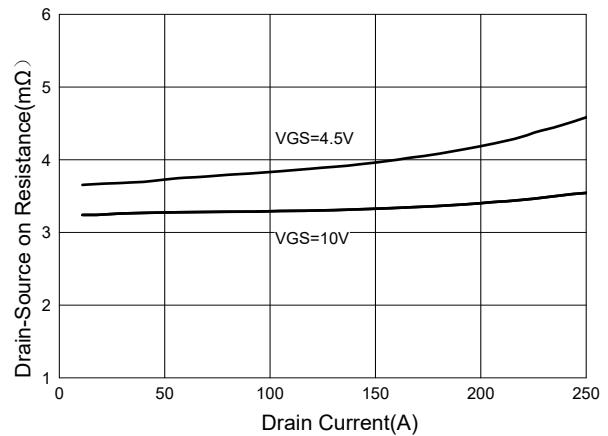


Fig.5 - Capacitance Characteristics

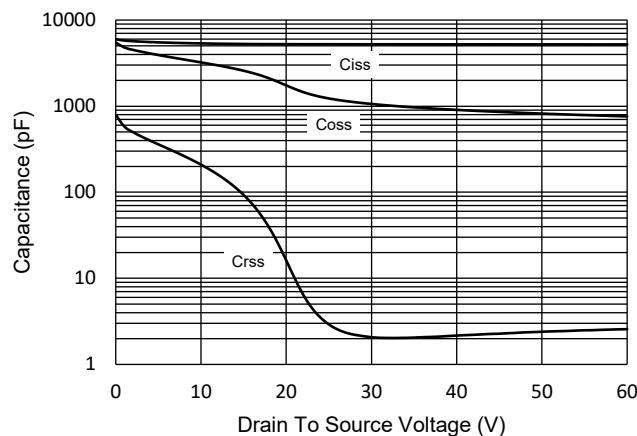
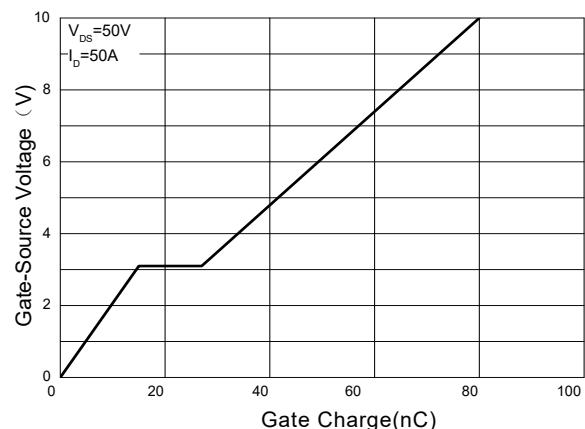


Fig. 6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

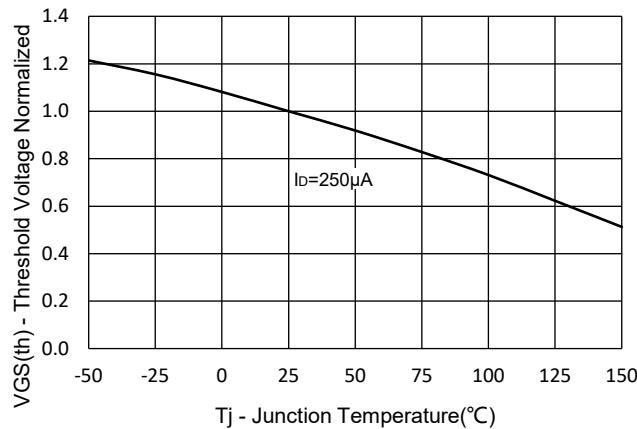


Fig.8 - Normalized On Resistance Characteristics

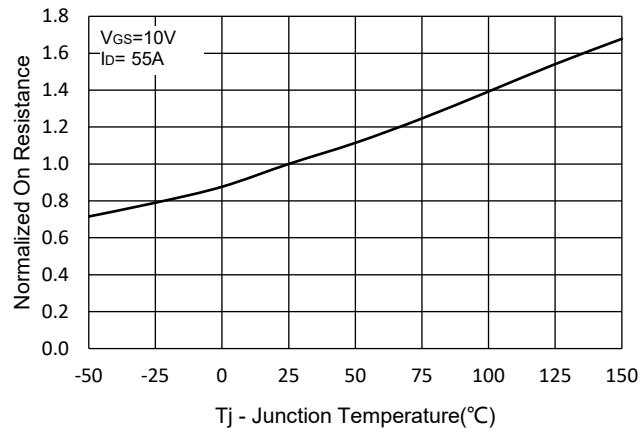


Fig.9 - I_S - V_{SD}

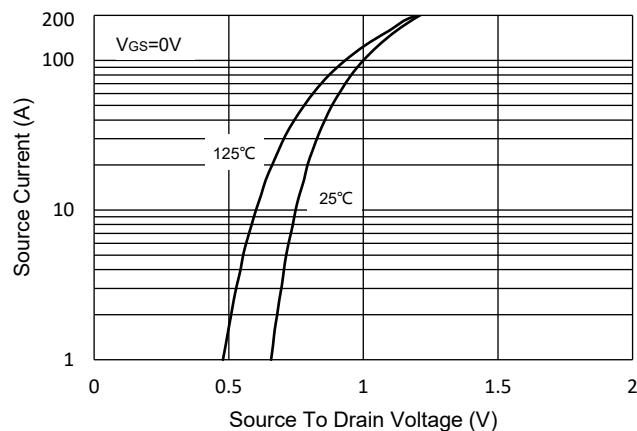


Fig. 10 - Drain Current

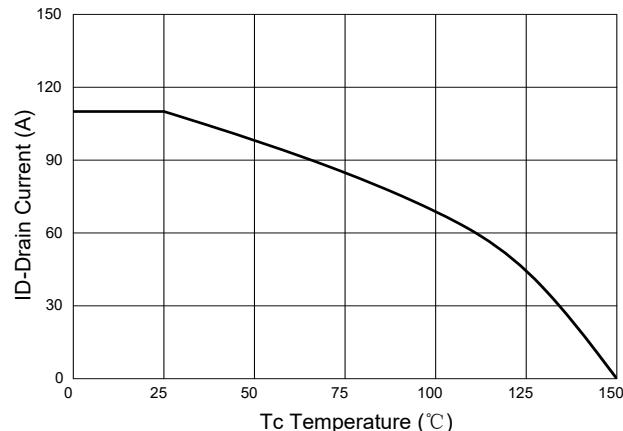
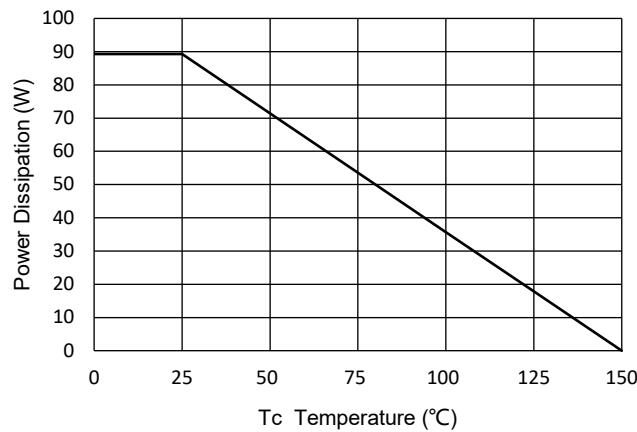
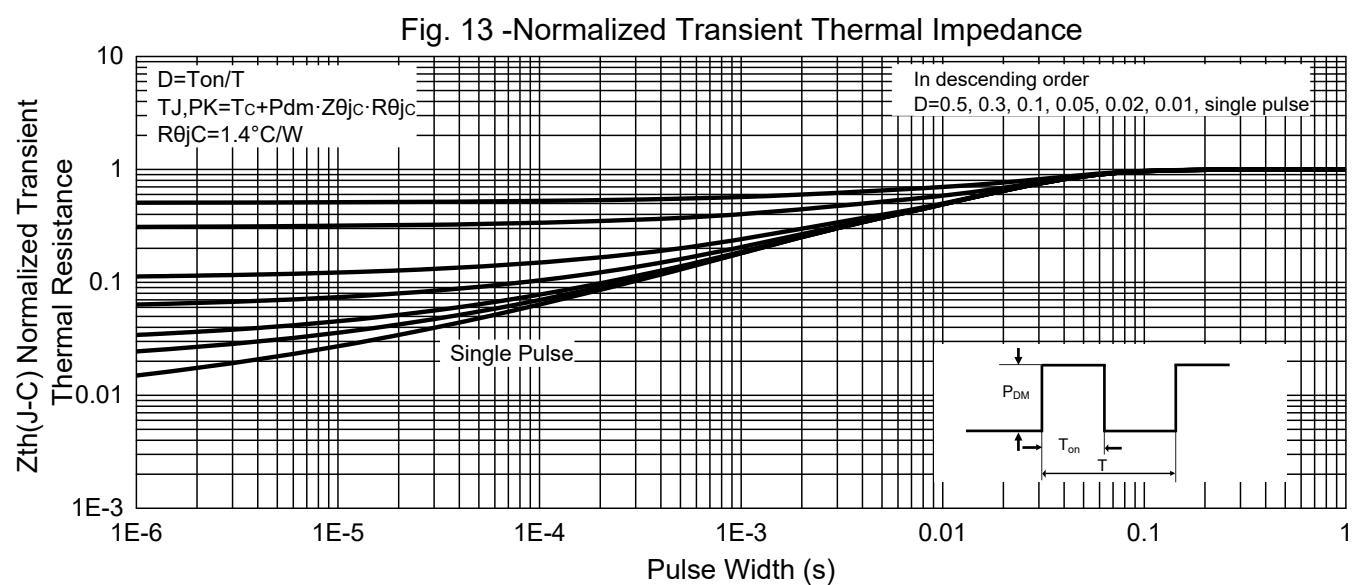
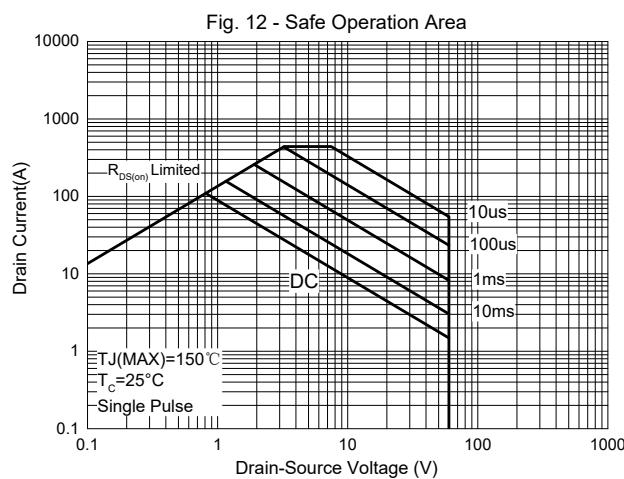


Fig.11 - PD Dissipation



Curve Characteristics



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel

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